NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE30P28Q uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or power management.

Application

●Power management

●Load switch

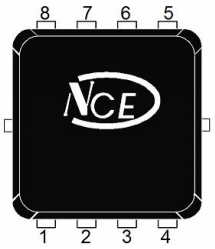
General Features

- V_{DS} = -30V,I_D = -28A
  $R_{DS(ON)}$ <9mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <17mΩ @ V_{GS}=-4.5V
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

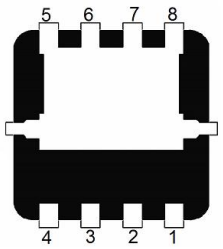
100% UIS TESTED!

100% ΔVds TESTED!

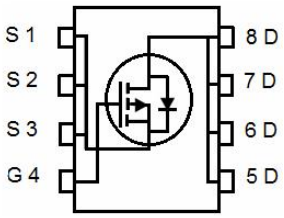
DFN 3.3X3.3



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30P28Q	NCE30P28Q	DFN3.3X3.3-8L	Ø330mm	12mm	5000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous		I_D	-28	A
Drain Current-Pulsed (Note 1)		I_{DM}	-80	A
Maximum Power Dissipation	TC=25°C	P_D	40	W
	TA=25°C		2	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	3.13	℃/W
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA

On Characteristics (Note 3)						
Parameter	**Symbol**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A	-	6.7	9	mΩ
	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-20A	-	9.5	17	
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	2691.7	-	PF
Output Capacitance	C_{oss}		-	492.3	-	PF
Reverse Transfer Capacitance	C_{rss}		-	362.3	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V, ID=-20A, V_{GS}=-10V,R_{GEN}=3Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	9.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-20A,V_{GS}=-10V	-	45.3	-	nC
Gate-Source Charge	Q_{gs}		-	6.1	-	nC
Gate-Drain Charge	Q_{gd}		-	13.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-28A	-	-	-1.2	V

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

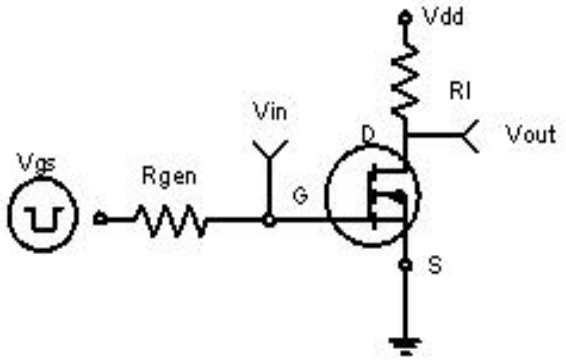


Figure 1 Switching Test Circuit

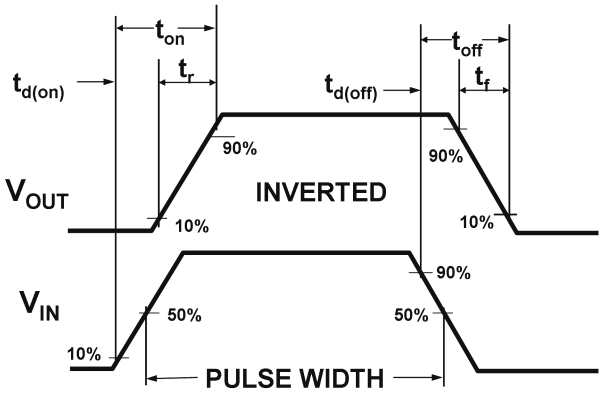


Figure 2 Switching Waveforms

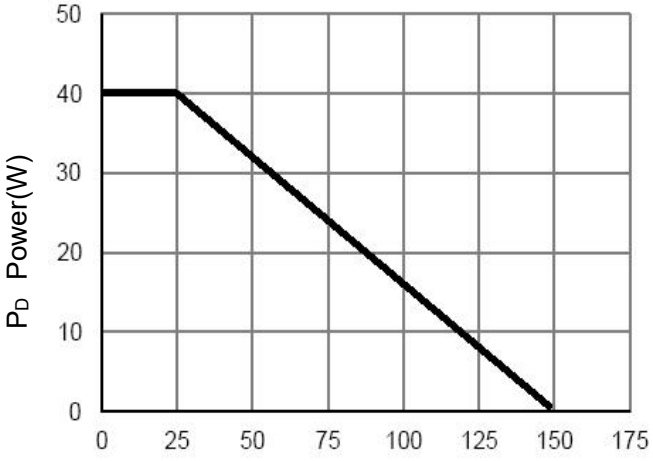


Figure 3 Power Dissipation

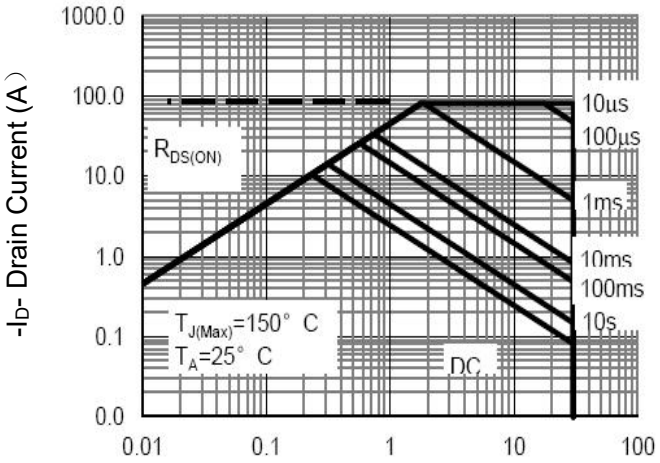


Figure 4 Safe Operation Area

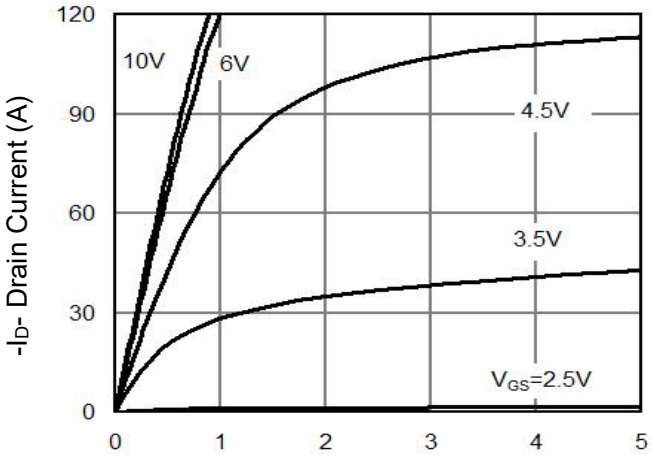


Figure 5 Output Characteristics

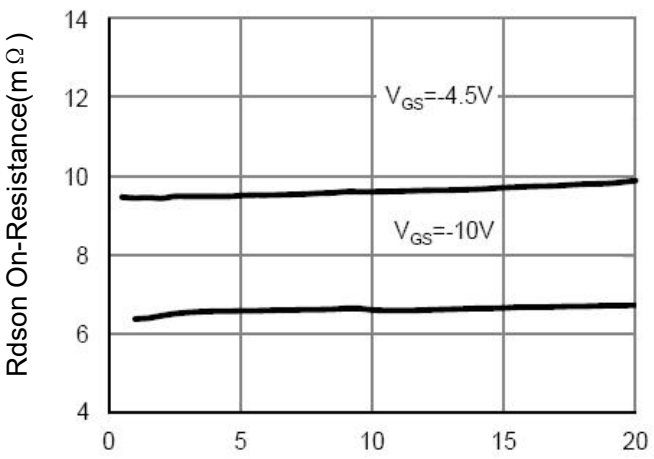


Figure 6 Drain-Source On-Resistance

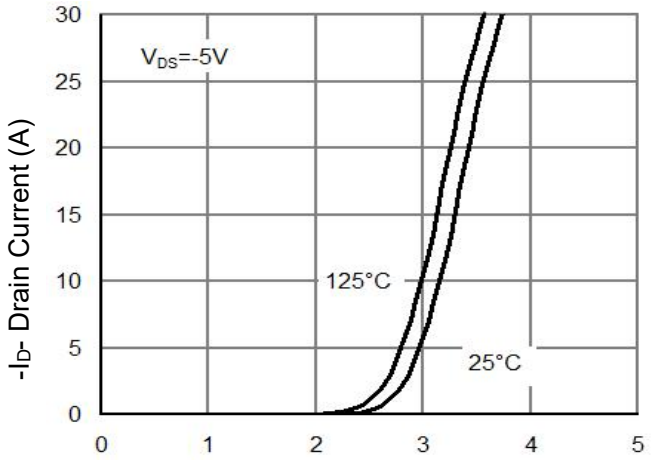


Figure 7 Transfer Characteristics

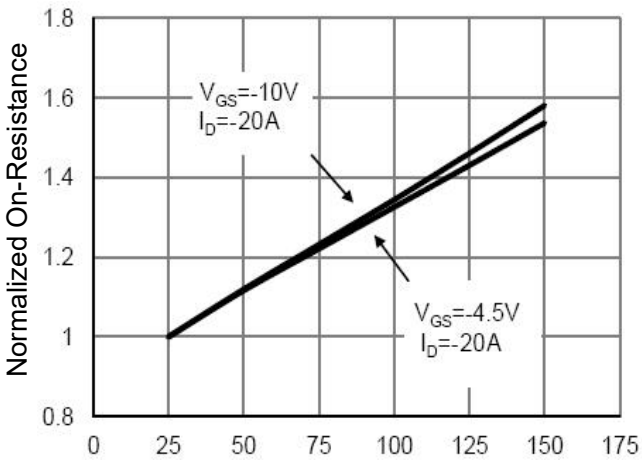


Figure 8 Drain-Source On-Resistance

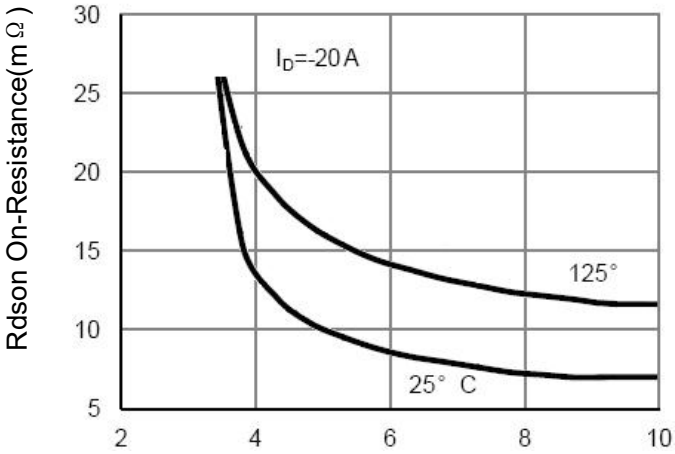


Figure 9 Rdson vs Vgs

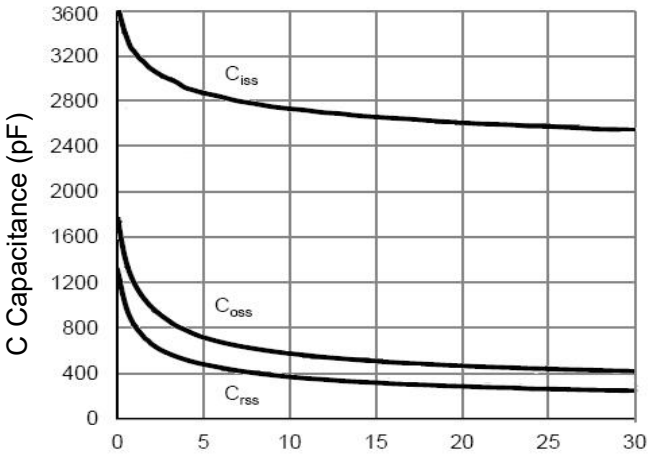


Figure 10 Capacitance vs Vds

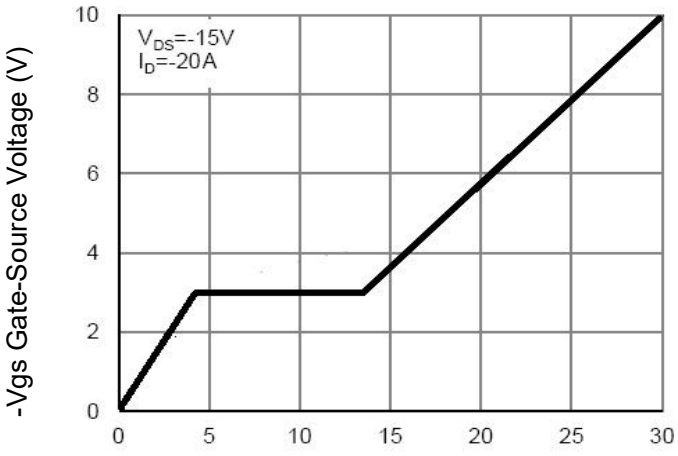


Figure 11 Gate Charge

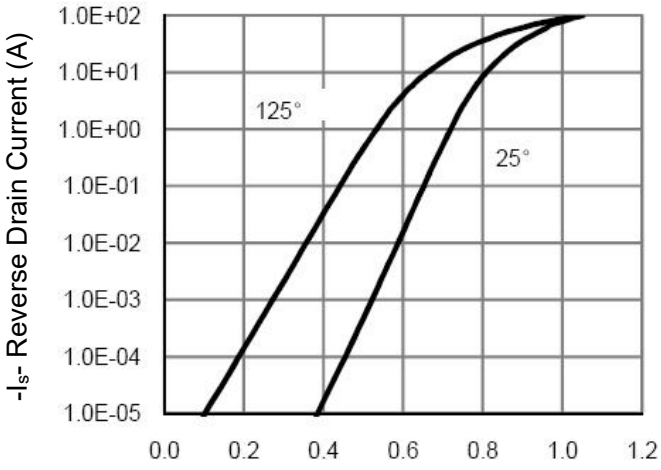


Figure 12 Source- Drain Diode Forward

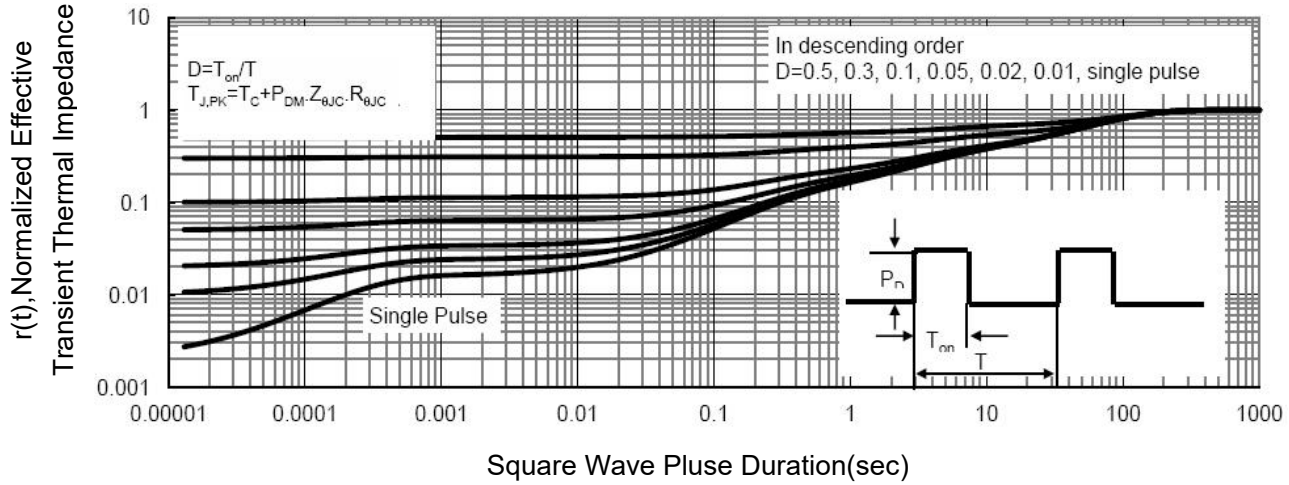


Figure 13 Normalized Maximum Transient Thermal Impedance

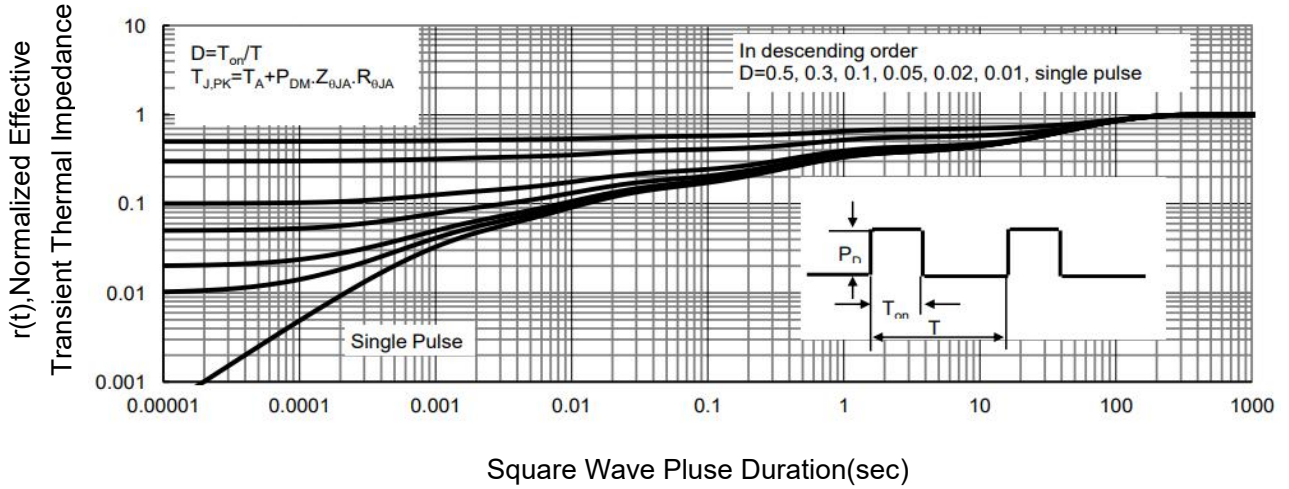
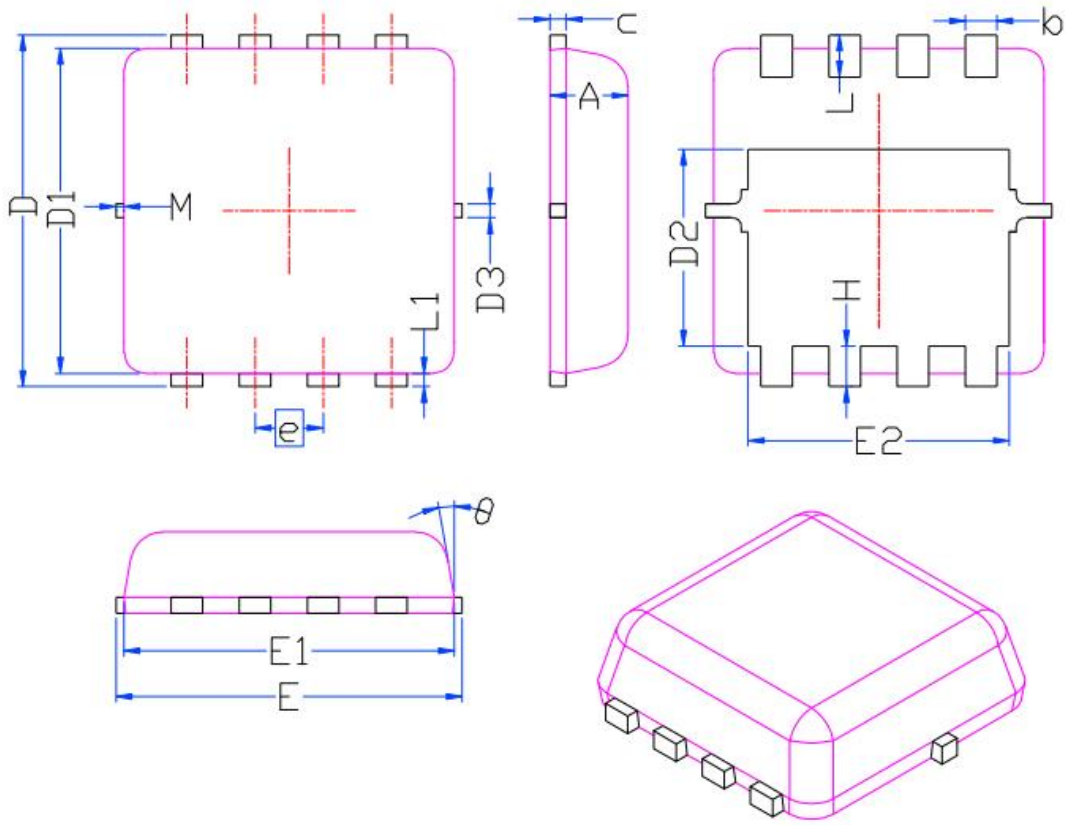


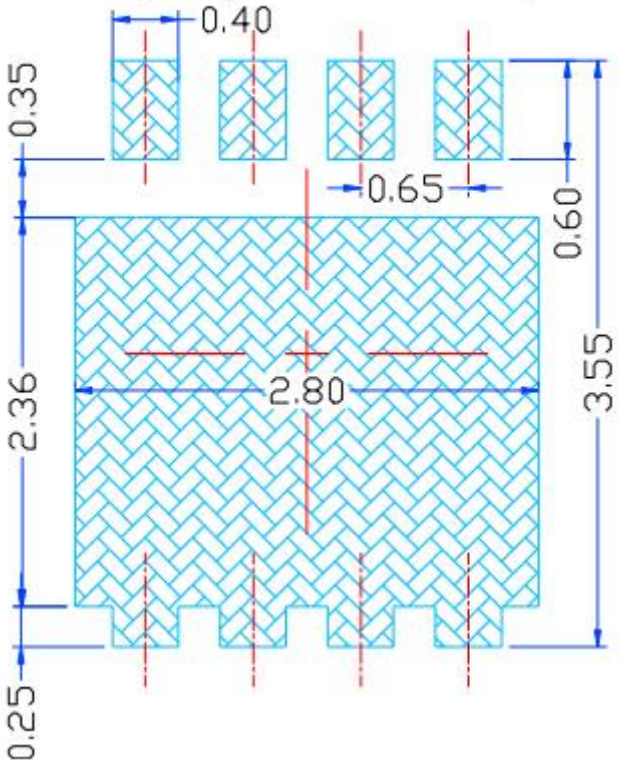
Figure 14 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	-	0.13	-
E	3.10	3.20	3.30
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

Land Pattern
(Only for Reference)



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